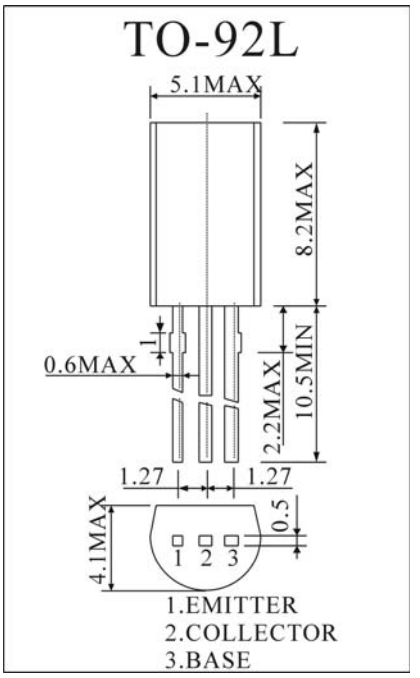
HUIZHOU JINSANE ELECTRONICS CO.,LTD

TO-92L Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)



FEATURES

Low speed switching

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	0.625	W
$R_{\Theta JA}$	Thermal Resistance, junction to Ambient	200	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA ,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -10mA , I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0			-1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-30V, I_B=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-1	μA
DC current gain	h_{FE}	V_{CE}= -6V, I_C= -1mA	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A, I_B= -0.2A			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-2A, I_B= -0.2A			-1.5	V
Transition frequency	f_T	V_{CE}= -5V, I_C=-0.1A f =10MHz	50	80		MHz

CLASSIFICATION OF h_{FE}

Rank	P
Range	200-400